



## **MXD8661**

SP6T for LTE diversity and RX



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### General Description

The MXD8661 is a low loss, high isolation SP6T switch for LTE diversity and RX applications.

The MXD8661 is compatible with +1.0V control logic, which is a key requirement for most cellular transceivers. This part is packaged in a compact 2mm x 2mm, 14-pin, QFN package which allows for a small solution size with no need for external DC blocking capacitors (when no external DC is applied to the device ports).

### Features

- Excellent insertion loss and isolation performance
  - 0.6 dB Insertion Loss at 2.7GHz
  - 28 dB Isolation at 2.7GHz
- Multi-Band operation 100MHz to 3000MHz
- Compact 2mm x 2mm in QFN-14 package
- No DC blocking capacitors required (unless external DC is applied to the RF ports)

### Applications

- 2G/3G/4G antenna diversity or LTE (FDD/TDD) receiving
- Cellular modems and USB Devices

### Functional Block Diagram and Pin Function

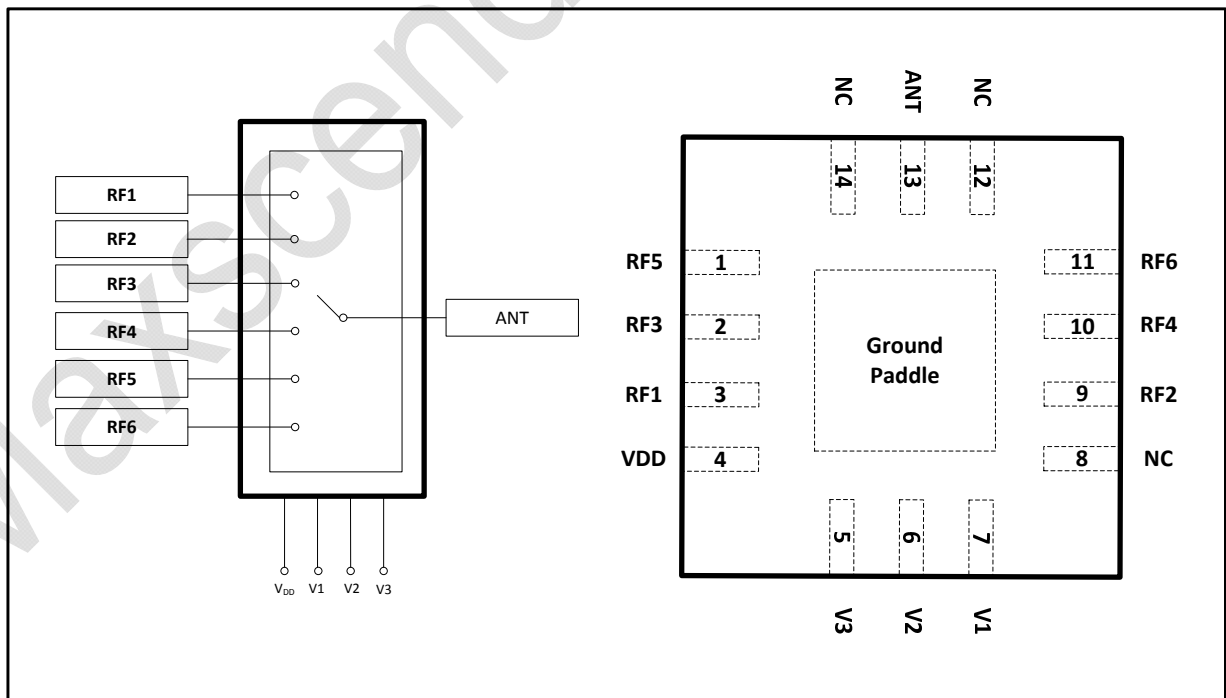


Figure 1 Functional Block Diagram and Pinout (Top View)

## Application Circuit

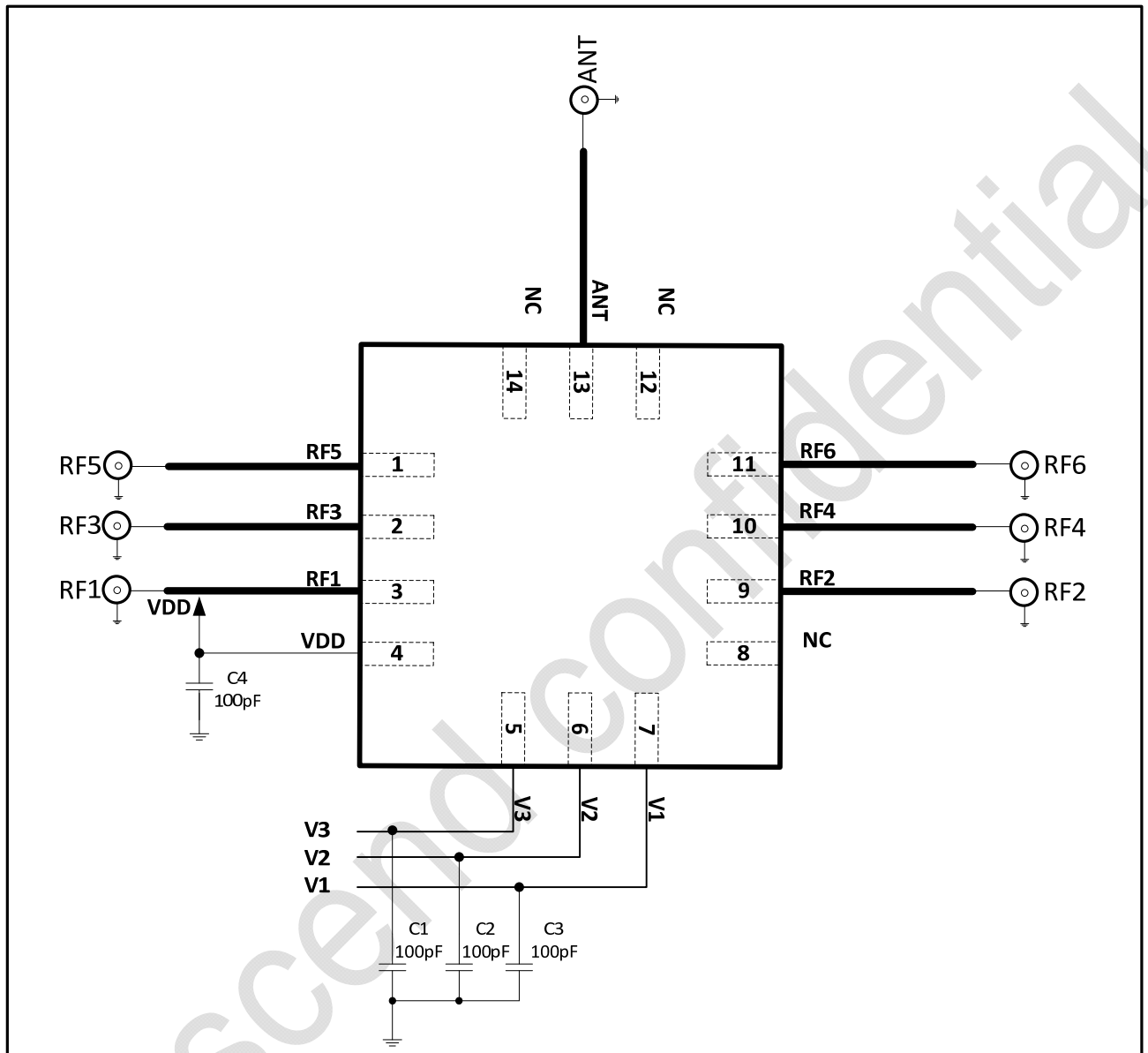


Figure 2 MXD8661 Evaluation Board Schematic

Table 1. Pin Description

Pin No.	Name	Description	Pin No.	Name	Description
1	RF5	RF port5	8	NC	No connection
2	RF3	RF port3	9	RF2	RF port2
3	RF1	RF port1	10	RF4	RF port4
4	V <sub>DD</sub>	Power supply	11	RF6	RF port6
5	V3	Control logic 3#	12	NC	No connection
6	V2	Control logic 2#	13	ANT	Antenna port
7	V1	Control logic 1#	14	NC	No connection
Ground Paddle	GND	Ground			

**Note:** Bottom ground paddles must be connected to ground.

**Truth Table**
**Table 2.**

Control pins			Switched RF Outputs					
V1	V2	V3	RF1	RF2	RF3	RF4	RF5	RF6
0	0	0	<b>Insertion Loss</b>	Isolation	Isolation	Isolation	Isolation	Isolation
0	0	1	Isolation	<b>Insertion Loss</b>	Isolation	Isolation	Isolation	Isolation
0	1	0	Isolation	Isolation	<b>Insertion Loss</b>	Isolation	Isolation	Isolation
0	1	1	Isolation	Isolation	Isolation	<b>Insertion Loss</b>	Isolation	Isolation
1	0	0	Isolation	Isolation	Isolation	Isolation	<b>Insertion Loss</b>	Isolation
1	0	1	Isolation	Isolation	Isolation	Isolation	Isolation	<b>Insertion Loss</b>
1	1	X	Isolation					

**Note:** “1” = 1.0 V to 3.0 V. “0” = 0 V to 0.3 V.

**Recommended Operation Range**
**Table 3. Recommended Operation Condition**

Parameters	Symbol	Min	Typ	Max	Units
Operation Frequency	f1	0.1	-	3.0	GHz
Power supply	V <sub>DD</sub>	2.5	2.8	3.0	V
Switch Control Voltage High	V <sub>H</sub>	1.0	1.8	3.0	V
Switch Control Voltage Low	V <sub>L</sub>	0	0	0.3	V

**Specifications**
**Table 4. Electrical Specifications**

Parameter	Symbol	Test Condition (Note 2)	Min	Typical	Max	Units
<b>DC Specifications</b>						
Supply voltage	V <sub>DD</sub>		2.5	2.8	3.0	V
Supply current	I <sub>DD</sub>			70	90	uA
Control voltage: High Low	V <sub>CTL_H</sub> V <sub>CTL_L</sub>		1.35	1.80	3.0 0.3	V V
Control current	I <sub>CTL</sub>	V <sub>CTL</sub> = 1.8 V		0.5	1.0	μ A
Switching Speed, on RF to another		10% to 90% RF		0.5	1	μs
Turn-on time	t <sub>on</sub>	Time from V <sub>DD</sub> =0V to part ON and RF at 90%		5	10	μs
<b>RF Specifications</b>						
Insertion loss (ANT pin to RF1/2/3/4/5/6 pins)	IL	0.1 to 1.0 GHz 1.0 to 2.0 GHz 2.0 to 2.7 GHz		0.50 0.55 0.60	0.50 0.60 0.70	dB dB dB
Isolation (ANT pin to RF1/2/3/4/5/6 pins)	Iso	0.1 to 1.0 GHz 1.0 to 2.0 GHz 2.0 to 2.7 GHz	35 30 24	40 35 28		dB dB dB
Input return loss (ANT pin to RF1/2/3/4/5/6 pins)	RL	0.1 to 1.0 GHz 1.0 to 2.0 GHz 2.0 to 2.7 GHz	20 18 15	25 22 20		dB dB dB
0.1 dB Compression Point (ANT pin to RF1/2/3/4/5/6 pins)	P0.1dB	0.8 GHz to 3.0 GHz		+28		dBm

**Absolute Maximum Ratings**

Table 5. Maximum ratings

Parameters	Symbol	Minimum	Maximum	Units
Supply voltage	V <sub>DD</sub>	2.5	+3.0	V
Control voltage (V1, V2, and V3)	V <sub>CTL</sub>	0	+3.0	V
RF input power (RF1 to RF6)	P <sub>IN</sub>		+28	dBm
Operating temperature	T <sub>OP</sub>	-20	+85	°C
Storage temperature	T <sub>STG</sub>	-40	+125	°C
Electrostatic Discharge, Human Body Model (HBM), Class 1C	ESD		1000	V

**Note:** Exposure to maximum rating conditions for extended periods may reduce device reliability. There is no damage to device with only one parameter set at the limit and all other parameters set at or below their nominal value. Exceeding any of the limits listed here may result in permanent damage to the device

## Package Outline Dimension

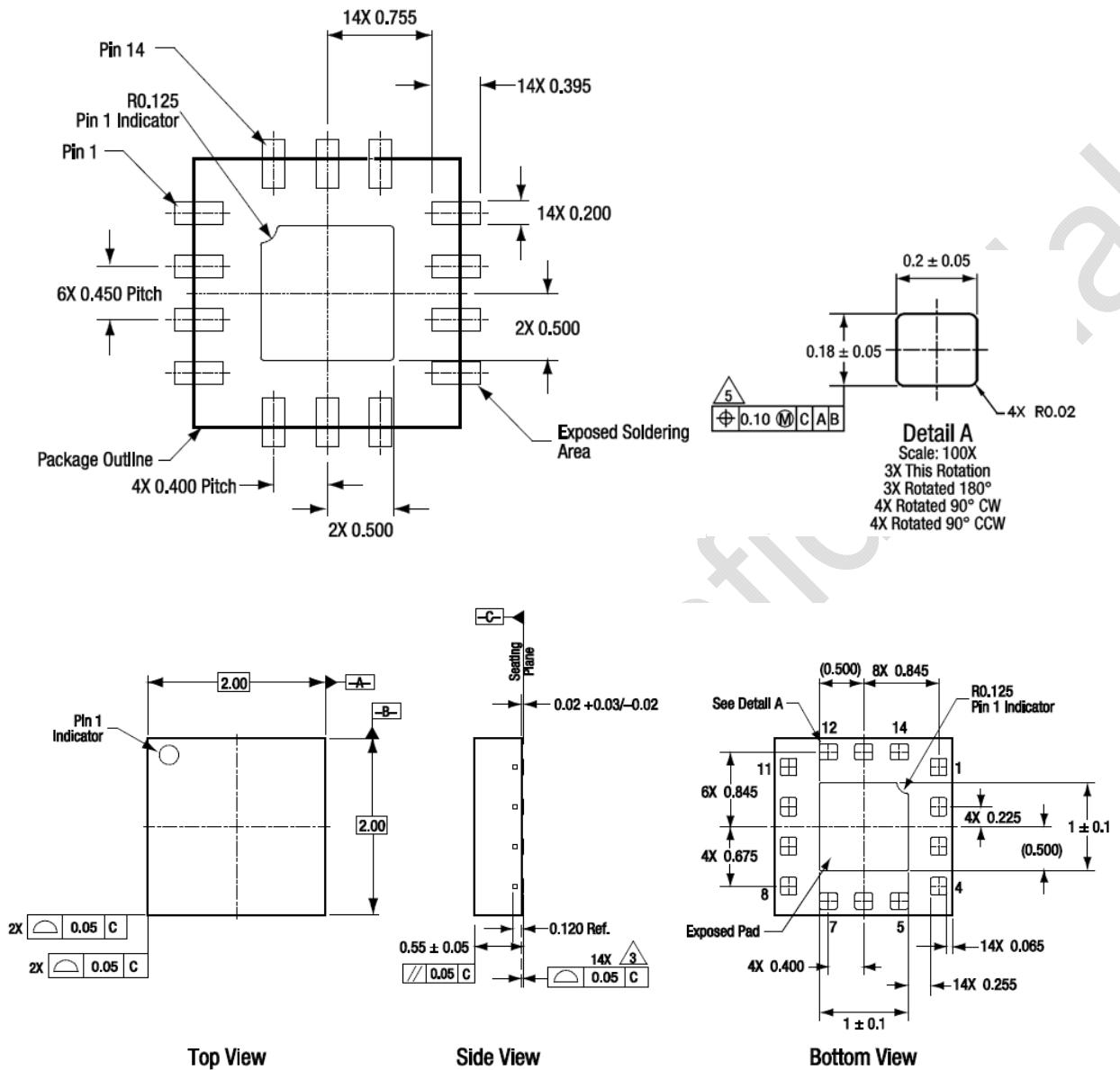


Figure 3 package outline dimension

## Reflow Chart

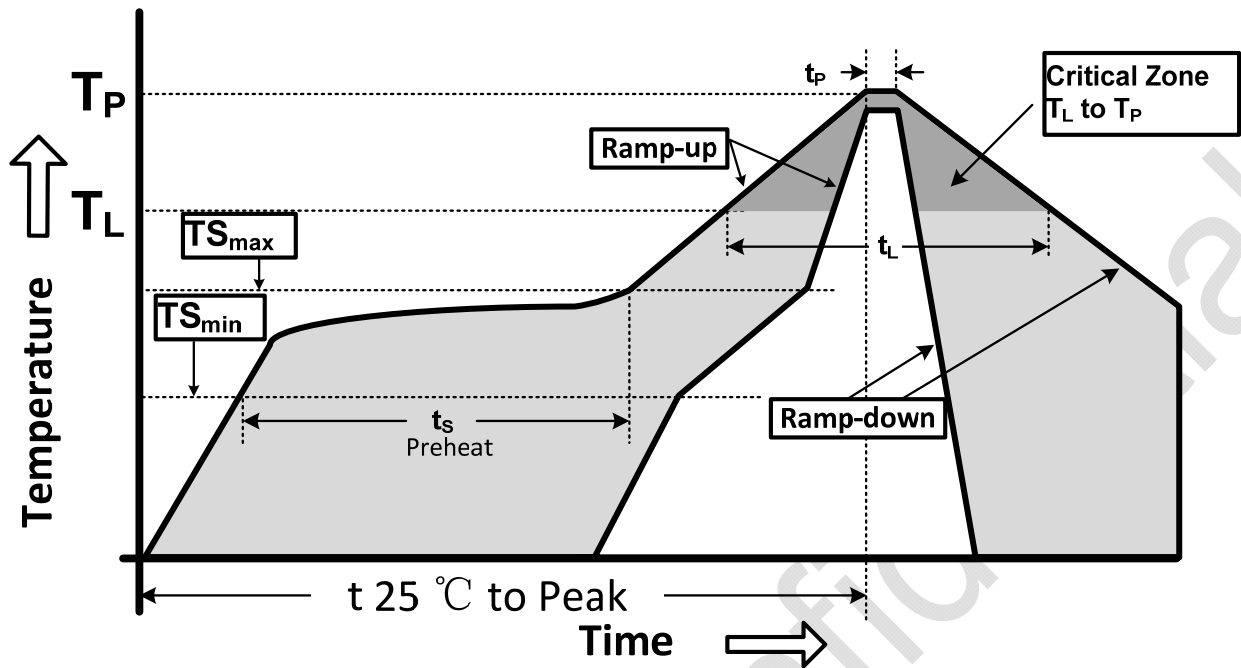


Figure 4 Recommended Lead-Free Reflow Profile

Table 6. Reflow condition

Profile Parameter	Lead-Free Assembly, Convection, IR/Convection
Ramp-up rate ( $TS_{max}$ to $T_p$ )	3°C/second max.
Preheat temperature ( $TS_{min}$ to $TS_{max}$ )	150°C to 200°C
Preheat time ( $t_s$ )	60 - 180 seconds
Time above $T_L$ , 217°C ( $t_L$ )	60 - 150 seconds
Peak temperature ( $T_p$ )	260°C
Time within 5°C of peak temperature( $t_p$ )	20 - 40 seconds
Ramp-down rate	6°C/second max.
Time 25°C to peak temperature	8 minutes max.

### ESD Sensitivity

Integrated circuits are ESD sensitive and can be damaged by static electric charge. Proper ESD protection techniques should be used when handling these devices.

### RoHS Compliant

This product does not contain lead, mercury, cadmium, hexavalent chromium, polybrominated biphenyls (PBB) and polybrominated diphenyl ethers (PBDE), and are considered RoHS compliant.